SUBJECT INDEX

Calcite 341
- $CaCO_3$–Li_2CO_3 phase diagram 342
- Crystallization, effect of hydrothermal solvents 353
- Dissolution in nitrate solutions 351
- Hydrothermal apparatus 358
- Hydrothermal growth 355
- Hydrothermal synthesis 344
- Infrared transmission 362
- Morphology of grown crystals 355
- Optical devices 341
- Solubility 344

Diamond 1
- Absorption spectroscopy 15
- Cathodoluminescence spectroscopy 16
- Epitaxial growth on diamond 7, 9
- Low temperature growth 3
- Microwave plasma enhanced CVD 3
- Raman spectroscopy 12
- SIMS analysis 12
- sp^2 bonded carbon 12
- Texture of polycrystalline film 10

Electron Emitters 153
- Carbide electron field emitters 165
- Field emission and ethylene exposure 169
- Field emission, Fowler–Nordheim plots 170, 171
- Floating zone growth 153
- $La_{1-x}Re_xB_6$ single crystals 162
- LaB_6 and $La_{1-x}Re_xB_6$ single crystals 160
- LaB_6 thermionic emission 174
- NbC<110> single crystal tip field emission 172
- Self Propogating High Temperature Synthesis (SHS) 156
- Stable emission currents 173
- TiC 155
- TiC electron field emitter 166
- TiC, NbC and LaB_6 153
- TiC<110> single crystal tip field emission 166
- Zone levelling single crystal growth 157
- Zone levelling, NbC 158

GaAs MESFETS and crystal growth 23
- GaAs
  - LEC technique 23
  - MESFETS 23
  - Model of EL2 and arsenic precipitation 65
  - Phase diagram 63
- GaAs(SI)
  - Arsenic interstitials 40
  - Cathodoluminescence 33
  - Dislocation-free GaAs 44
  - Dislocations and electrical uniformity 54
  - Dislocations in LEC-GaAs 42
  - EL2 distribution 28
  - Fully Encapsulated LEC (FEC LEC) 47
  - Hall effect and photoluminescence 29
  - Impurity hardening with In 45
  - Inhomogeneities due to dislocations 25, 29
  - Leakage currents (GaAs wafers) 26
  - Macroscopic uniformity, source drain current and threshold voltage 34
  - Microscopic uniformity 35
  - Model of annealing and EL2 distribution 59
  - Post growth annealing and EL2 distribution 56
  - Sheet carrier concentration 32, 33
  - Striation avoidance with VM FEC 50
  - Surface defects suppression 47
  - Threshold voltage and FET performance 36
  - Threshold voltage and dislocations 36
  - Threshold voltage and dopants 36

Threshold voltage, dopants, dislocations and FET performance 36
Threshold voltage (V_{th}) for FETs 24
Vertical magnetic field FEC LEC 50
V_{th} scattering mechanism 38
V_{th} scattering mechanism and EL2 distribution 62

High T_c Bulk Superconductors 179
$Ba_{1-x}K_xBiO_3$ 182
$Ba_{1-x}K_xBiO_3$ single crystals 191
$BaPb_{1-x}Bi_xO_3$ 182
$BaPb_{1-x}Bi_xO_3$ single crystals 191, 194
Bi-Sr-Ca-Cu-O system 187
Bi-Sr-Ca-CuO and the Tl-Ba-Ca-CuO systems 211
Bulk single crystals 181
Crucible contamination 216
Crystallographic structure 182
Detwinning 218
Inhomogeneous dopant distribution 205
$La_{2-x}M_xCuO_4$ (M=Ba, Sr, Ca) 184
La_2CuO_4 based single crystals 194
La_2O_3-CuO and La_2O_3-SrO-CuO phase diagrams 194
$Ln_1Ba_2Cu_3O_7$ (123 phase) single crystal growth 209
$Ln_1Ba_2Cu_3O_7$ (Ln=rare earth) single crystals 206
$Ln_1Ba_2Cu_3O_x$ 185
$Ln_1Ba_2Cu_3O_x$ with Bi and Tl 186
$M_{2-x}Ce_xCuO_{4+\delta}$ (M=Nd, Sm, Eu, Pr) single crystal growth 201, 204
$M_{2-x}Ce_xCuO_{4+d}$ (M=Nd, Sm, Eu, Pr) single crystals 199
Nd_2O_3-CeO_2-CuO phase diagram 200
Perovskite structure 183
Single crystal growth (bulk) 188
Skull Melt Method 191
Slow cooling technique 189
Tl-Ba-Ca-Cu-O and single crystal growth 215, 216
Tl-Ba-Ca-Cu-O phase diagram 215
Top Seeded Solution Growth Technique (TSSG) 190
Travelling Solvent Floating Zone (TSFZ) 190
$Y_2Ba_4Cu_8O_{16-x}$, $Y_2Ba_4Cu_7O_{15-x}$ single crystal growth 210
Y_2O_3-BaO-CuO phase diagram 206

High Tc Thin Film Superconductors 224
Defects in epitaxial films 232
Epitaxial growth by MBE 236
Epitaxial growth by laser ablation 235
Epitaxial growth by reactive evaporation 236
Single crystal growth 226
Sputtering, face to face epitaxial growth 228
Sputtering, ion beam 232
Sputtering, negative ion bombardment 227
Sputtering, off axis or off center 231
Substrate materials 238
Ultra thin films and superlattices 237

Organic crystals 369
Crystal growth 375, 400
2-methyl-4-nitroaniline (MNA) 409
Amino acids 408
Anthracene 400
Aromatic crystals 400
Benzil 406
Benzophenone 405
Chalcone crystals 409
Deuterated *l*-arginine phosphorate 408
Diacetylene (PTS) 407
Epitaxial growth 410
GeO phthalocyanine (GeOPc) 410
l-Arginine phosphorate monohydrate 408
Long chain crystals 406
n-Octadecanol 407
Non-linear optic crystals 408
p-Terphenyl 405
Phthalocyanine metal derivatives 410
Stearic acid 407
Superconducting crystals 411
Tetraoxane 406
Thienylchalcone crystals 409
Crystal structure and lattice parameter 401, 402
Defect control 375, 411
Diffusion, self and impurity 374
Dislocation motion 387
Dislocation slip systems 389
Dislocations 378

Annealing 403
Direct observation 382
Simulated molecular structure 392
Photoplastic effect 392, 393
Planar defects 396
Point defects 369
Direct observation 376
Simulation 375
Positron trapping rate 373
Stacking faults 396
Twinning 399
Vacancy entropy 372

Quartz 313
Crystal growth in NaC1, KC1 and pure water 333
Crystal growth, effects of impurities 333
Defects 320
Defects in Y cut section 321
Devices 314
Dislocations, lattice distortion and Q values 326
Electrodiffusion 332
Frequency, dependence on temperature 327
Growth and characteristics 313
Growth of high quality crystals 317
Light scattering and impurities 325
Light scattering tomography 320, 324
Line defects 328
Line defects by X-ray topography 330
Optical devices 315
Q values 318
Solid inclusions 328
Transmission and absorption factor α 320
Y-bar crystal 318
Z-plate crystal 318

Radiation Detectors 245
Absorption coefficient 250
Alkali halides (NaI:T1, CsI:Tl) 256
$Bi_4Ge_3O_{12}$ 270
Bismuth germanium oxide 252
CdO-WO_3 system, phase diagram 262
$CdWO_4$ 272
Crystal growth BGO 258
Crystal growth $CdWO_4$ 262
Crystal growth of scintillator crystals 256
Detectors for high energy physics 290
Detectors for light pulses 295
Detectors for nuclear physics 288
Detectors for solar (v) neutrino detectors 296
Detectors for UV and VUV applications 296
Detectors for well logging 287
Electronic transitions 249
Electron trapping 277
Excitation and emission spectra 252
Gd_2O_3-SiO_2 phase diagram 266
Gd_2SiO_5: Ce 264
Gd_2SiO_5: Ce 273
Light emission, light output 251
Positron emission 254, 284
Radiation damage 276
Radiation hardness BGO 279
Radiation hardness BaF_2 281
Radiation hardness CsI:Tl 279
Radiation hardness CsI:pure 279
Radiation hardness GSO:Ce 282
Radiation hardness NaI:Tl 278
Radiation hard scintillators 297
$Bi_4Si_3O_{12}$ (BSO) 297
CeF_3 298
for very high energies, CdF_2 299
Radiation length 251
Scintillation characteristics 246, 253, 368
Scintillation characteristics NaI, CsI 268
Scintillation detectors 253
Scintillation detectors for high energy physics 255
Scintillation detectors for nuclear physics 255
Scintillator applications 284
X-ray computed tomography 284

SiC 127
Blue LED 127
4H SiC external quantum efficiency 140
4H SiC I/V characteristics 143
4H SiC wavelength emission 144
6H SiC and electrical characteristics 139
electroluminescence 138
structure 139
Carrier concentration 133
Doping 132
Full colour LED lamp 145
Hall mobility 133
LPE for LEDs 135

Lely method 130
Polytypes 128, 132
Sublimation growth 129
Temperature dependence of growth rate 130

Thin film compound semiconductors (GaAs and related III–Vs) 73
Arsenic surface coverage and reconstruction 99
As source molecules, decomposition rate 86
Atomic Layer Controlled Epitaxy (ALCE) 76, 87
Atomic Layer Epitaxy 87
Compound Semiconductor (III–V) 73
Electron mobility (2D) in MD structures 112
GaAs on Si and strained layer superlattices 116
Growth on vicinal surfaces 101
HEMT (enhancement mode/depletion mode) 109
Heterojunction bipolar transistors 108
MBE, MOCVD characteristics 76
Migration Enhanced Epitaxy 92
Modulation doped AlGaAs/GaAs heterostructure 106, 111
Photoluminescence spectra, A1As/GaAs quantum wells 80
Reflection Difference Spectroscopy (RDS) 81, 82
RHEED in MBE 78
RHEED in MEE 95
Role of RDS and SPA in ALE 90
Surface photoabsorption (SPA) 81, 83
Thickness control in epitaxial growth 75, 76
Thickness control in MBE, RHEED oscillations 78
Thickness control in MOCVS 82
Thickness variation 108